

A 60 GHz CMOS Power Amplifier Using Capacitive Cross-Coupling Neutralization with 16% PAE

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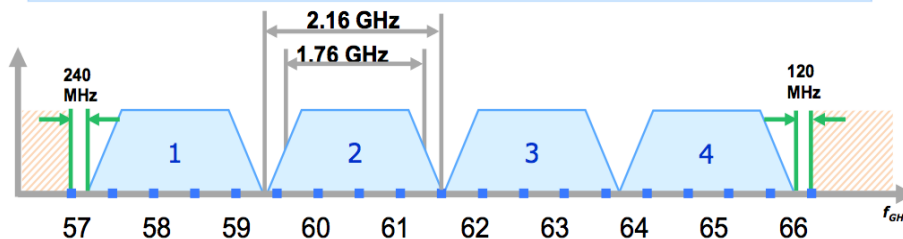
- **Back Ground**
- **Capacitive Cross-Coupling Neutralization**
- **3-stage Power Amplifier**
- **Measurement Result**
- **Conclusion**

60GHz CMOS direct-conversion transceiver for multi-Gbps wireless communication

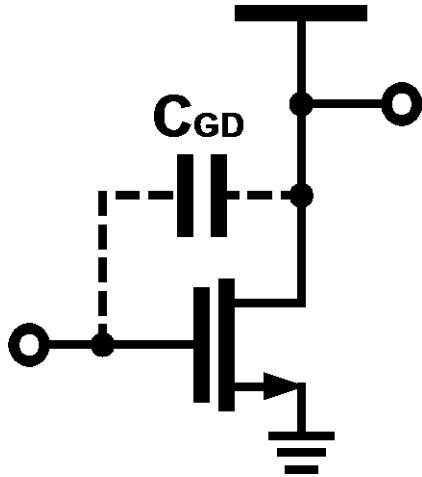
IEEE 802.15.3c specification

- 57.24GHz - 65.88GHz
- 2.16GHz/ch x 4channels
- QPSK → 3.5Gbps/ch
- **16QAM → 7.0Gbps/ch**

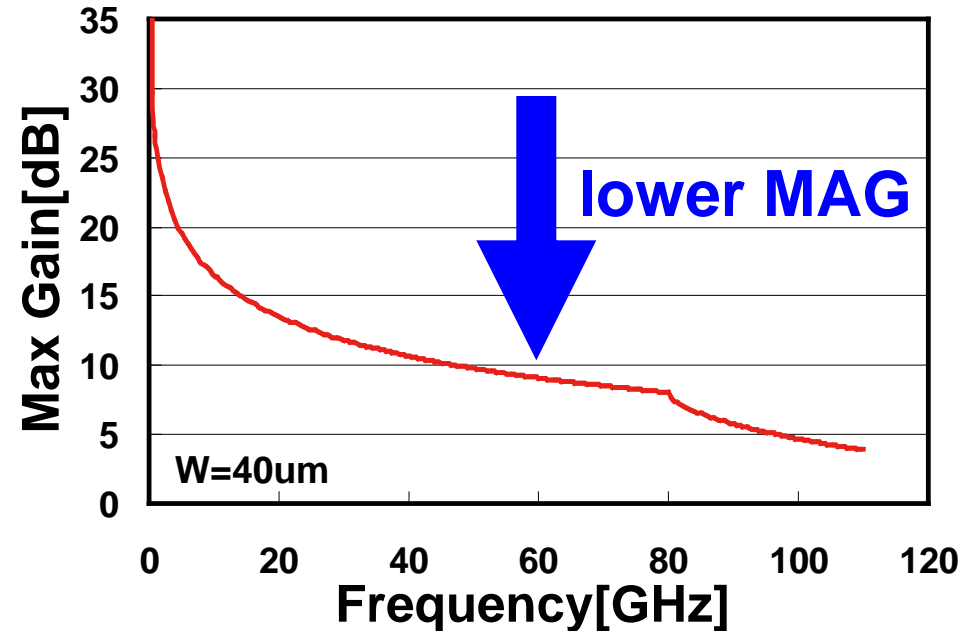
Channel Number	Low Freq. (GHz)	Center Freq. (GHz)	High Freq. (GHz)	Nyquist BW (GHz)	Roll-Off Factor
A1	57.24	58.32	59.40	1.76	0.227
A2	59.40	60.48	61.56	1.76	0.227
A3	61.56	62.64	63.72	1.76	0.227
A4	63.72	64.80	65.88	1.76	0.227



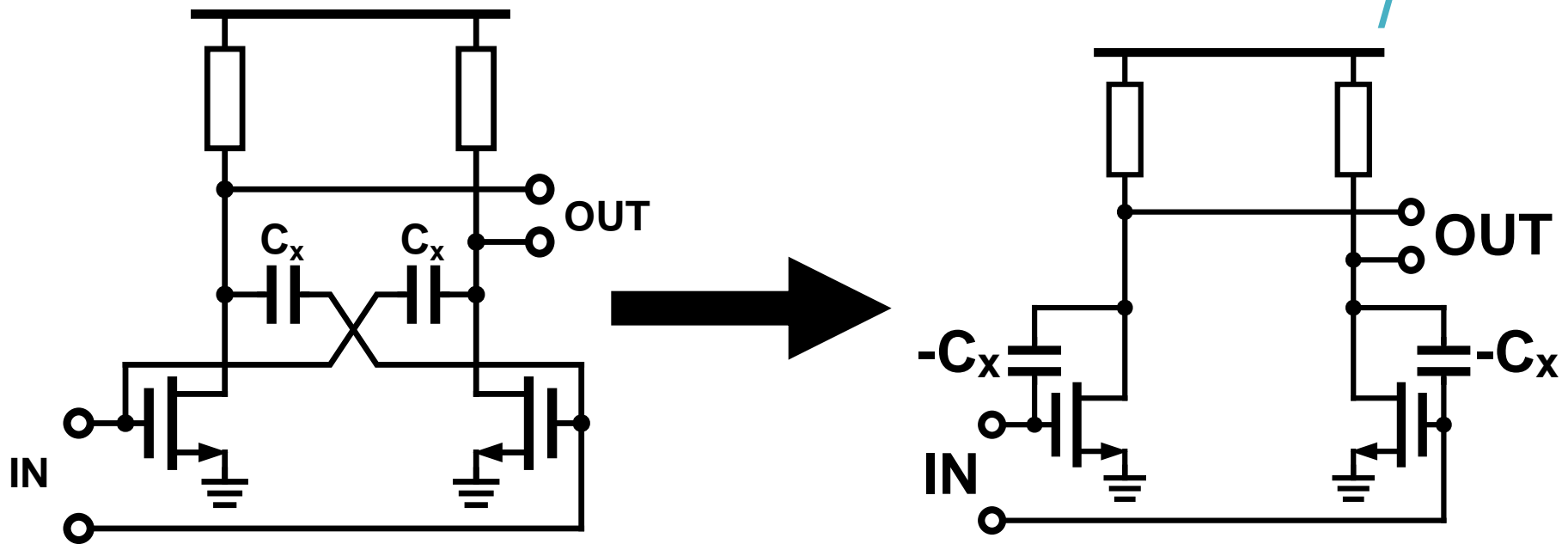
Parasitic Capacitance



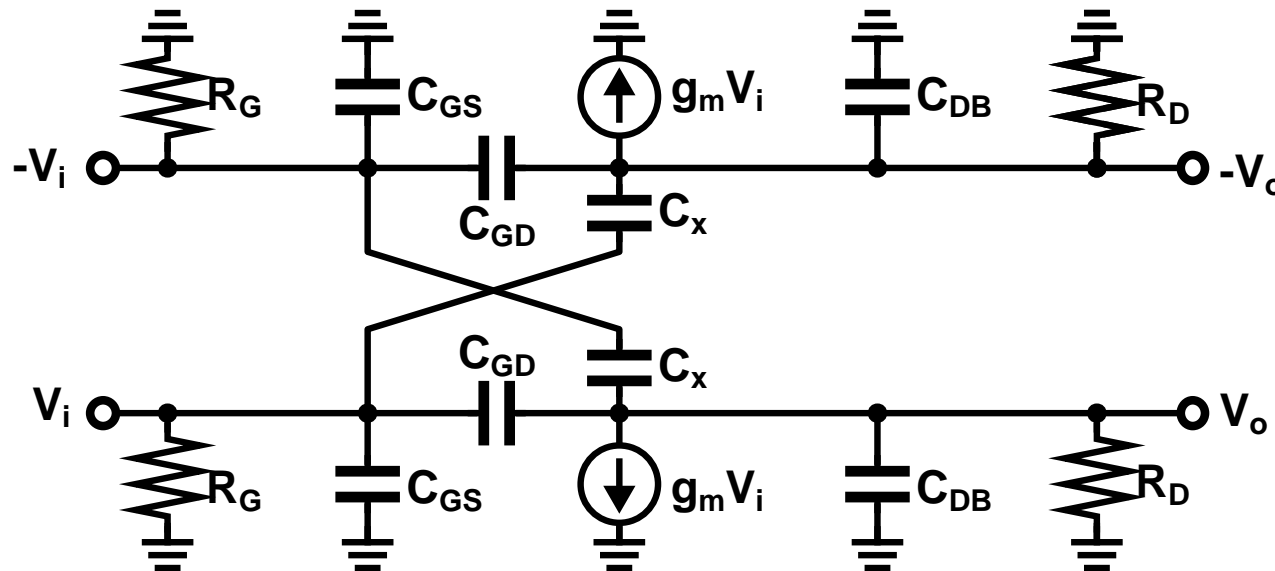
$$C_{GD} = -\frac{\text{Im}[Y_{12}]}{j\omega}$$



- Parasitic Capacitances causes low reverse isolation.



- **A cross-coupled capacitor between gate and drain of the opposite-side transistor works as negative capacitor.**
 - The reverse isolation is improved.

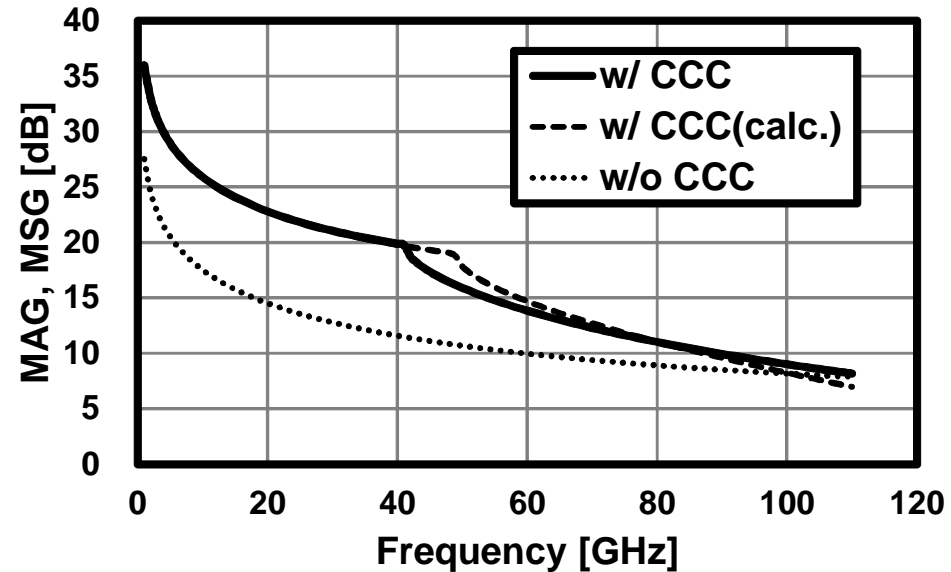
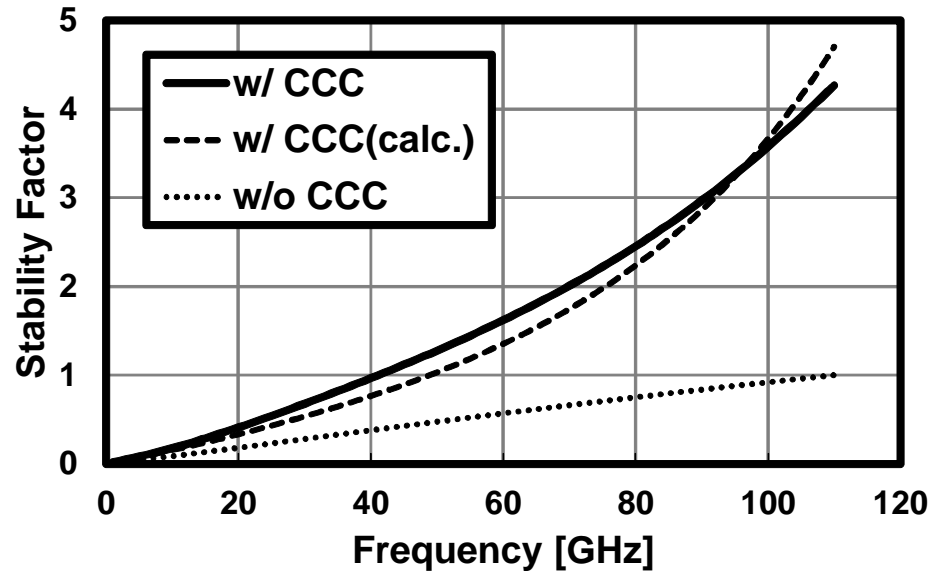


Stability

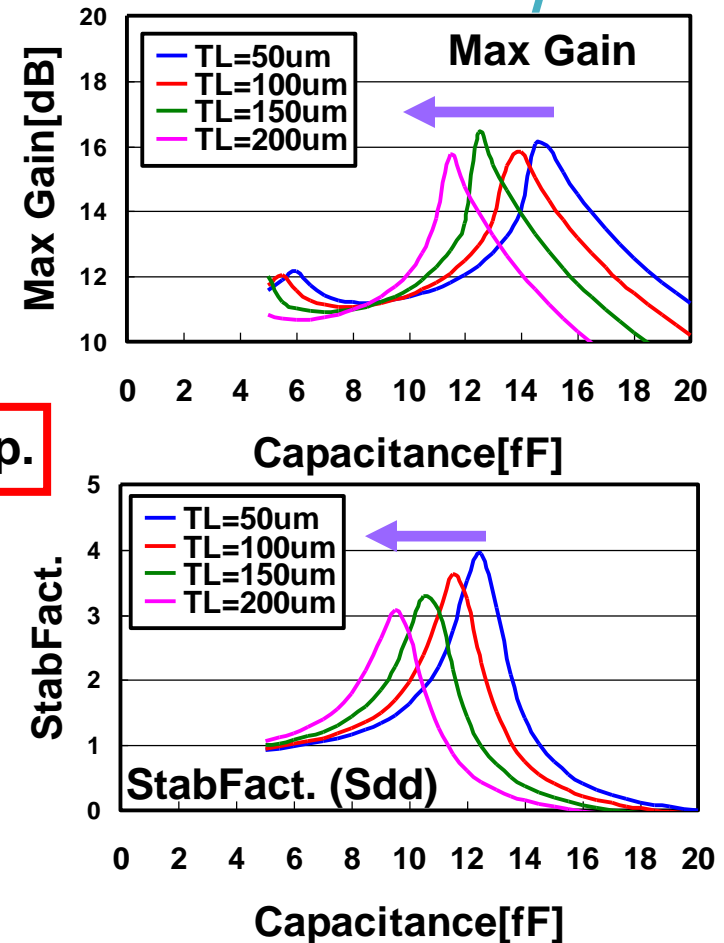
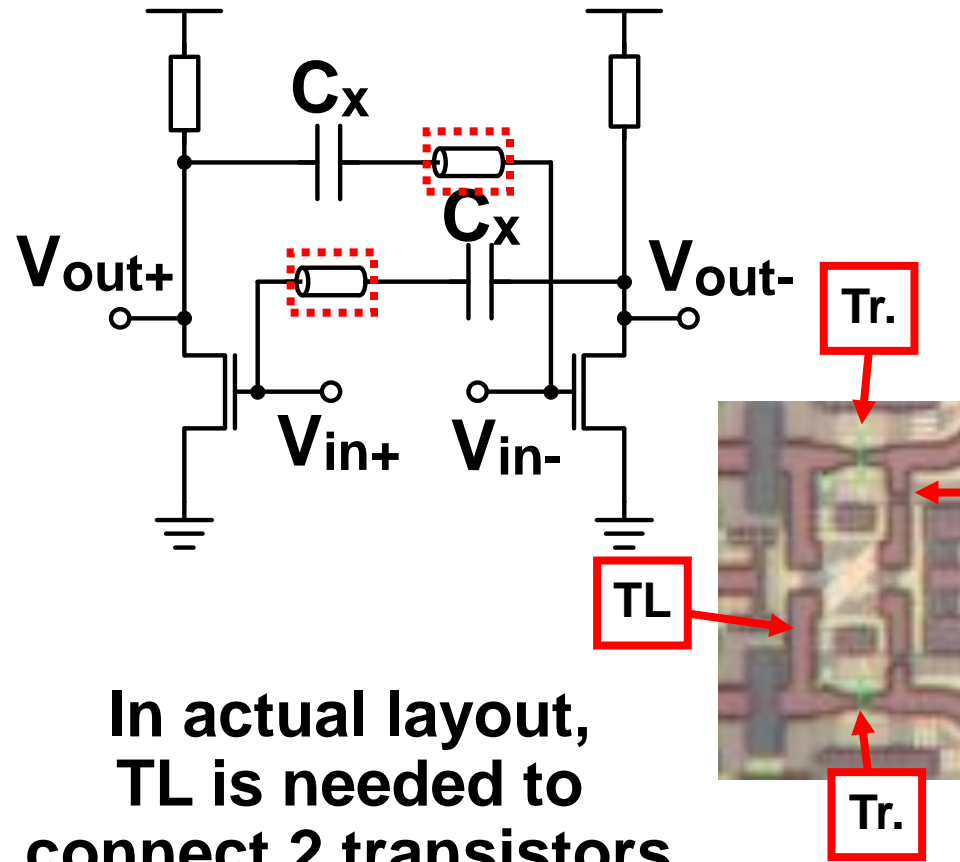
$$k = \frac{2\text{Re}[Y_{11}]\text{Re}[Y_{22}] - \text{Re}[Y_{12}Y_{21}]}{|Y_{12}Y_{21}|} = \frac{2 + \omega^2(C_{GD} - C_X)^2 R_G R_D}{\omega |C_{GD} - C_X| R_G R_D \sqrt{\omega^2(C_{GD} - C_X)^2 + g_m^2}}$$

Maximum Available Gain

$$\text{MAG} = \left| \frac{Y_{21}}{Y_{12}} \right| (k - \sqrt{k^2 - 1}) = \frac{\sqrt{\omega^2(C_{GD} - C_X)^2 + g_m^2}}{\omega |C_{GD} - C_X|} (k - \sqrt{k^2 - 1})$$



- **Stability Factor is improved across entire frequency.**
- **The maximum available gain is improved about 5dB at 60GHz**

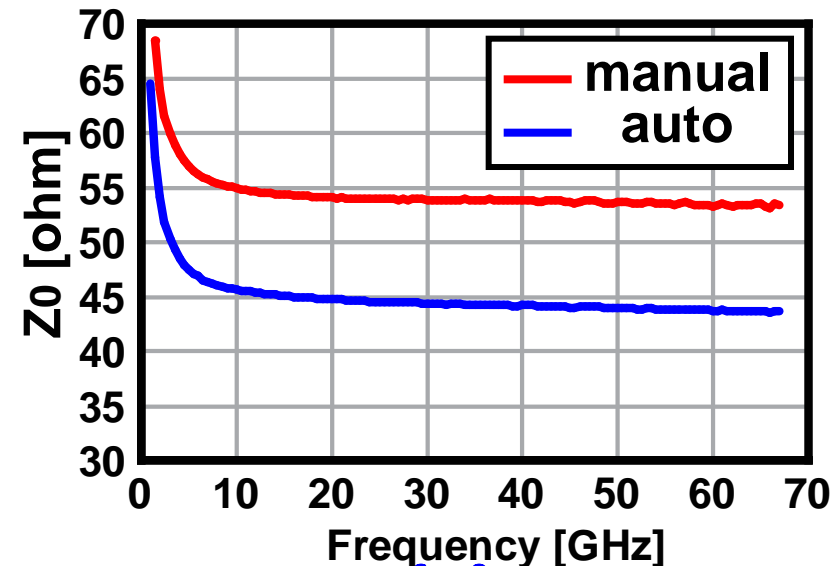
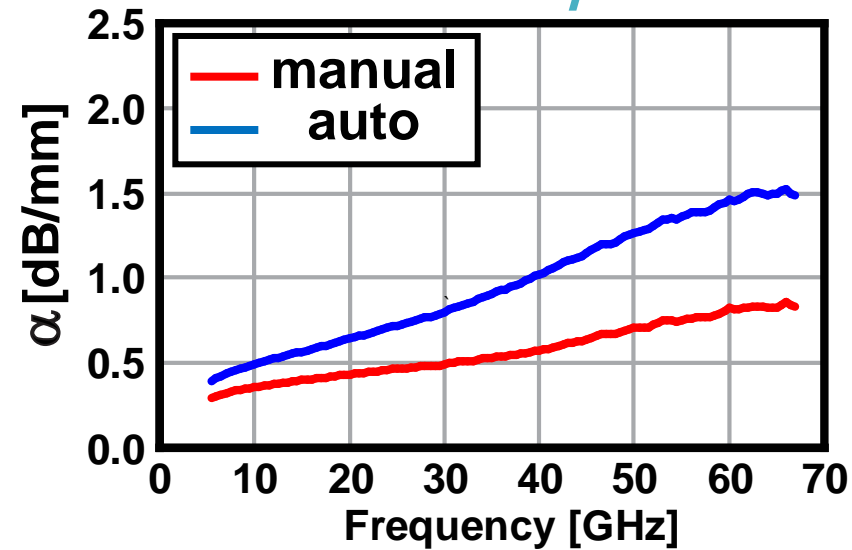
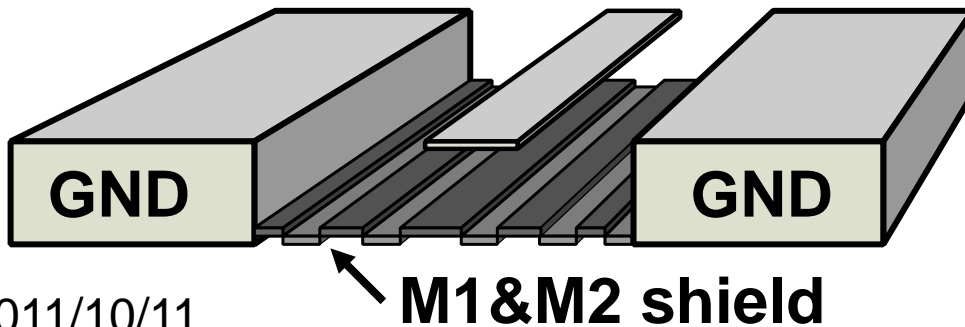
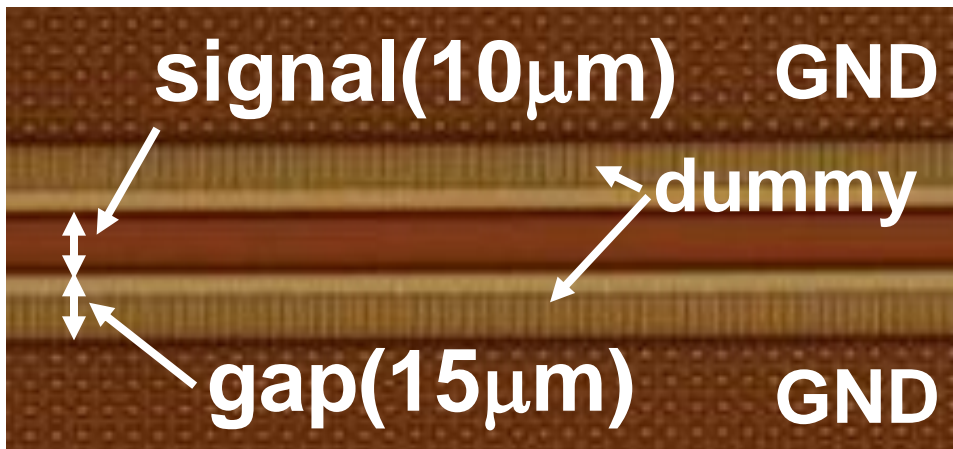


In actual layout,
TL is needed to
connect 2 transistors.

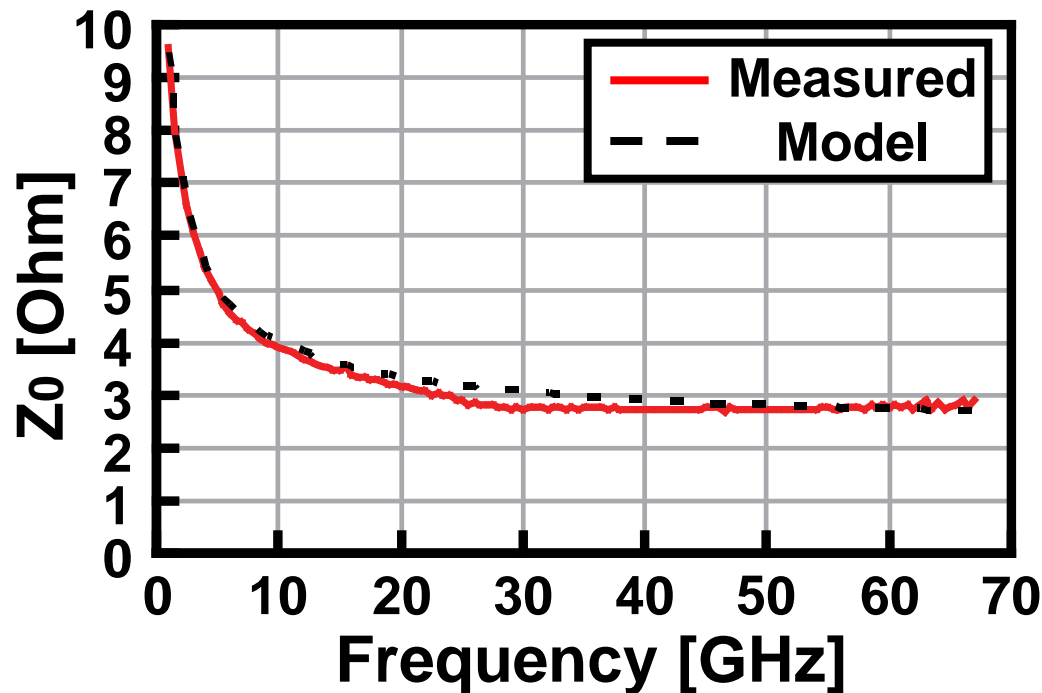
- The longer TL, The smaller capacitance to cross-couple is needed.

Transmission line

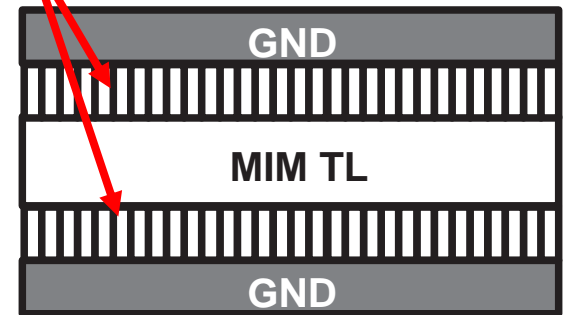
- Low loss(0.8dB/mm)
- Dummy metals are manually placed.



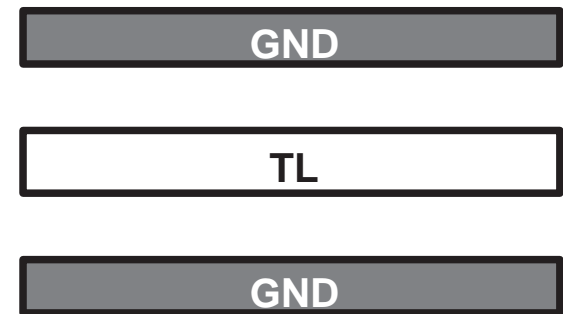
- De-coupling use
- Modeling accuracy
- Avoiding self-resonance of parallel-plate capacitors



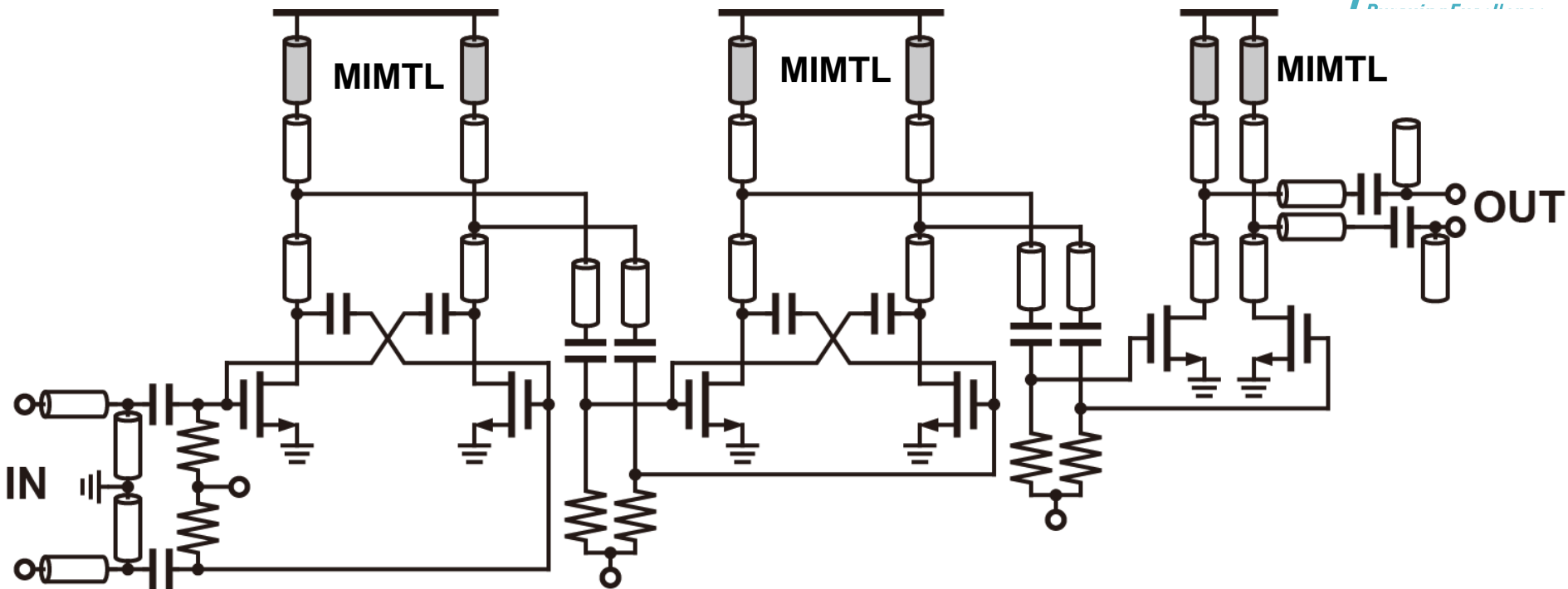
MIM capacitor



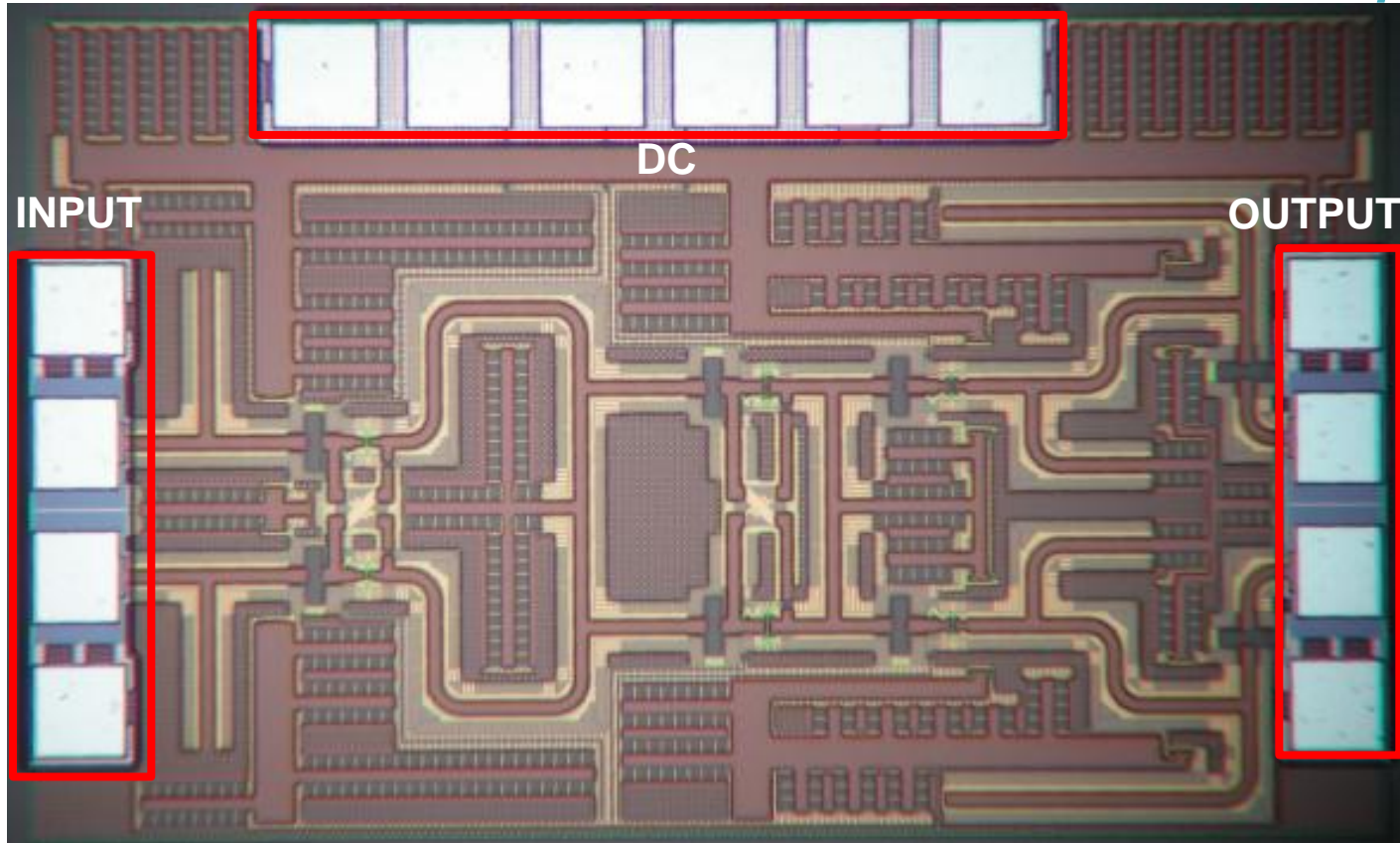
MIM transmission line



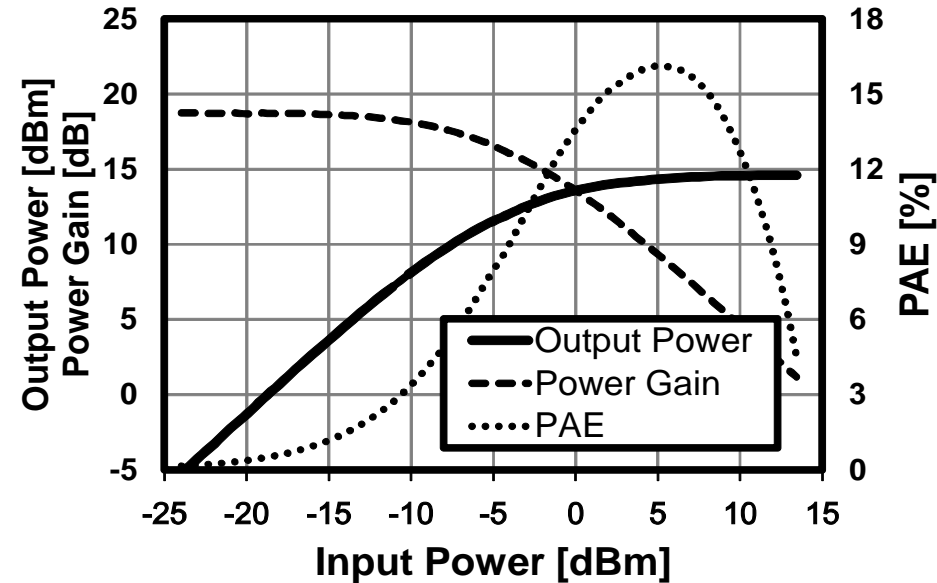
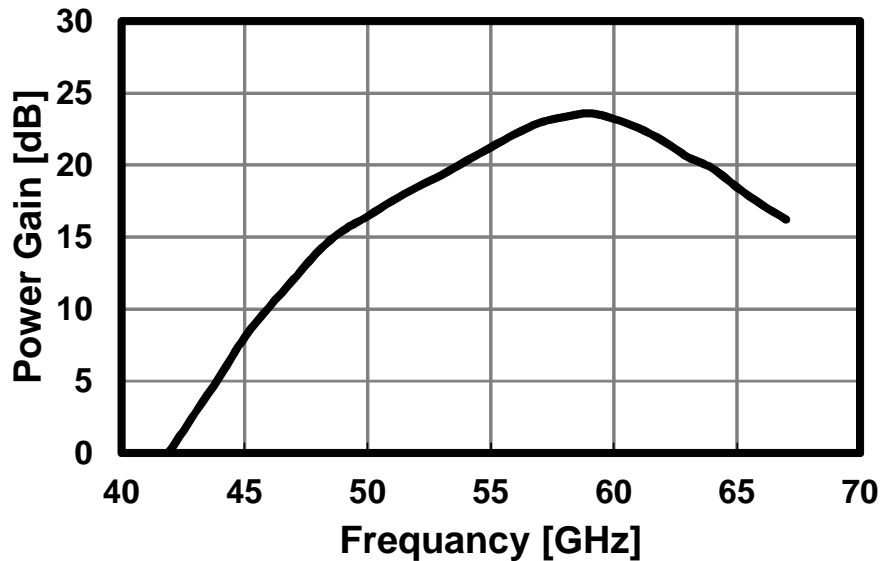
50 Ω transmission line



- 3-stage differential power amplifier.
- The capacitive cross-coupling neutralization is used.
- The guided micro-strip line is used for matching network.
- The de-coupling is implemented as MIM TL.



- Core area: 1.0mmx0.6mm



- **Power Gain: 23.2dB**
- **P_{sat} : 14.6dBm**
- **$P_{1\text{dB}}$: 10.0dBm**
- **Power Consumption: 135mW ($V_{\text{dd}}=1.2\text{V}$)**
- **Peak PAE: 16.3%**

	Power Gain [dB]	P_{1dB} [dBm]	P_{sat} [dBm]	Peak PAE [%]	Power [mW]	V_{DD} [V]
ISSCC 2008[5]	5.5	9	12.3	8.8	-	1.0
ISSCC 2009[3]	16	2.5	11.5	11	43.5	1.0
ISSCC 2010[6]	20.6	18.2	19.9	14.2	-	1.2
ISSCC 2010[7]	19.2	14.1	17.7	11.1	480	1.0
ISSCC 2010[8]	14.3	11	16.6	4.9	732	1.2
ISSCC 2011[9]	20.3	15	18.6	15.1	-	1.0
This Work	23.2	10.0	14.6	16.3	135	1.2

[5] D. Chowdhury, *ISSCC*, 2008 [6] C. Y. Law, *ISSCC*, 2010

[7] J. Lai, *ISSCC*, 2010 [8] B. Martineau, *ISSCC*, 2010 [9] J.Chen, *ISSCC*, 2011

- A 60GHz power amplifier using the capacitive cross-coupling neutralization with the low-loss transmission line is presented.
- The 3-stage differential power amplifier in 65nm CMOS achieves power gain of 23.2dB, output power at 1-dB compression point of 10.0dBm, saturated output power of 14.6dBm, peak PAE of 16.3% and power consumption of 135mW.